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a capacitor upper electrode formed integrally with the drain electrode on the capacitor lower electrode;

a first insulation film inserted between the capacitor upper electrode and the capacitor lower electrode; and

a thin film transistor array substrate connected with the drain electrode and including a reflective electrode formed at the pixel areas and formed above and connected to the drain electrode.

5. (Amended) A transflective liquid crystal display device, which has pixel areas defined into a reflection part and a transmission part, the liquid crystal display device comprising:

a plurality of gate lines and data lines intersecting on a first substrate, the gate lines and the data lines defining pixel areas;

a plurality of thin film transistors formed at the intersections of the gate lines and the data lines, each thin film transistor including a gate electrode, a semiconductor layer, a source electrode and a drain electrode;

a capacitor lower electrode of a storage capacitor formed on the same plane as a gate line; a capacitor upper electrode formed integrally with the drain electrode on the capacitor lower electrode;

a first insulation film inserted between the capacitor upper electrode and the capacitor lower electrode;

a reflective electrode connected with the drain electrode and formed on the reflection area above the drain electrode; and

a thin film transistor array substrate connected with the reflective electrode and including the transmissive electrode formed at the transmission area.



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7. (Amended) The transflective liquid crystal display device as claimed in claim 5, wherein the first insulation film is one of silicon nitride (SiNx) and silicon oxide (SiOx).



9. (Amended) The transflective liquid crystal display device as claimed in claim 8, wherein the second insulation film is one of silicon nitride (SiNx), BCB or acryl resin.